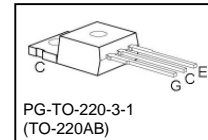
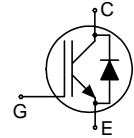


## Fast IGBT in NPT-technology with soft, fast recovery anti-parallel Emitter Controlled Diode

- 75% lower  $E_{off}$  compared to previous generation combined with low conduction losses
- Short circuit withstand time – 10  $\mu$ s
- Designed for:
  - Motor controls
  - Inverter
- NPT-Technology for 600V applications offers:
  - very tight parameter distribution
  - high ruggedness, temperature stable behaviour
  - parallel switching capability
- Very soft, fast recovery anti-parallel Emitter Controlled Diode
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC<sup>1</sup> for target applications
- Complete product spectrum and PSpice Models : <http://www.infineon.com/igbt/>



Type	$V_{CE}$	$I_C$	$V_{CE(sat)}$	$T_j$	Marking	Package
SKP02N60	600V	2A	2.2V	150°C	K06N60	PG-TO-220-3-1

### Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CE}$	600	V
DC collector current	$I_C$	6.0	A
$T_C = 25^\circ\text{C}$		6.0	
$T_C = 100^\circ\text{C}$		2.9	
Pulsed collector current, $t_p$ limited by $T_{jmax}$	$I_{Cpuls}$	12	
Turn off safe operating area	-	12	
$V_{CE} \leq 600\text{V}, T_j \leq 150^\circ\text{C}$			
Diode forward current	$I_F$	6.0	
$T_C = 25^\circ\text{C}$		6.0	
$T_C = 100^\circ\text{C}$		2.9	
Diode pulsed current, $t_p$ limited by $T_{jmax}$	$I_{Fpuls}$	12	
Gate-emitter voltage	$V_{GE}$	$\pm 20$	V
Short circuit withstand time <sup>2</sup>	$t_{SC}$	10	$\mu$ s
$V_{GE} = 15\text{V}, V_{CC} \leq 600\text{V}, T_j \leq 150^\circ\text{C}$			
Power dissipation	$P_{tot}$	30	W
$T_C = 25^\circ\text{C}$			
Operating junction and storage temperature	$T_j, T_{stg}$	-55...+150	$^\circ\text{C}$
Soldering temperature	$T_s$	260	$^\circ\text{C}$
wavesoldering, 1.6 mm (0.063 in.) from case for 10s			

<sup>1</sup> J-STD-020 and JESD-022

<sup>2</sup> Allowed number of short circuits: <1000; time between short circuits: >1s.

**Thermal Resistance**

Parameter	Symbol	Conditions	Max. Value	Unit
<b>Characteristic</b>				
IGBT thermal resistance, junction – case	$R_{thJC}$		4.2	K/W
Diode thermal resistance, junction – case	$R_{thJCD}$		7	
Thermal resistance, junction – ambient	$R_{thJA}$	PG-TO-220-3-1	62	

**Electrical Characteristic, at  $T_j = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
<b>Static Characteristic</b>						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=500\mu A$	600	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C=2A$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$	1.7 -	1.9 2.2	2.4 2.7	
Diode forward voltage	$V_F$	$V_{GE}=0V, I_F=2.9A$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$	1.2 -	1.4 1.25	1.8 1.65	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=150\mu A, V_{CE}=V_{GE}$	3	4	5	
Zero gate voltage collector current	$I_{CES}$	$V_{CE}=600V, V_{GE}=0V$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$	- -	- -	20 250	$\mu A$
Gate-emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V$	-	-	100	nA
Transconductance	$g_{fs}$	$V_{CE}=20V, I_C=2A$	-	1.6	-	S
<b>Dynamic Characteristic</b>						
Input capacitance	$C_{iss}$	$V_{CE}=25V,$ $V_{GE}=0V,$ $f=1\text{MHz}$	-	142	170	pF
Output capacitance	$C_{oss}$		-	18	22	
Reverse transfer capacitance	$C_{riss}$		-	10	12	
Gate charge	$Q_{Gate}$	$V_{CC}=480V, I_C=2A$ $V_{GE}=15V$	-	14	18	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	$L_E$		-	7	-	nH
Short circuit collector current <sup>2)</sup>	$I_{C(SC)}$	$V_{GE}=15V, t_{SC}\leq 10\mu s$ $V_{CC}\leq 600V,$ $T_j\leq 150^\circ\text{C}$	-	20	-	A

<sup>2)</sup> Allowed number of short circuits: <1000; time between short circuits: >1s.

**Switching Characteristic, Inductive Load, at  $T_j=25\text{ }^\circ\text{C}$** 

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>IGBT Characteristic</b>						
Turn-on delay time	$t_{d(on)}$	$T_j=25\text{ }^\circ\text{C}$ , $V_{CC}=400\text{V}$ , $I_C=2\text{A}$ , $V_{GE}=0/15\text{V}$ , $R_G=118\Omega$ , $L_{\sigma}^{1)}=180\text{nH}$ , $C_{\sigma}^{1)}=180\text{pF}$ Energy losses include "tail" and diode reverse recovery.	-	20	24	ns
Rise time	$t_r$		-	13	16	
Turn-off delay time	$t_{d(off)}$		-	259	311	
Fall time	$t_f$		-	52	62	
Turn-on energy	$E_{on}$		-	0.036	0.041	mJ
Turn-off energy	$E_{off}$		-	0.028	0.036	
Total switching energy	$E_{ts}$		-	0.064	0.078	

**Anti-Parallel Diode Characteristic**

Diode reverse recovery time	$t_{rr}$	$T_j=25\text{ }^\circ\text{C}$ , $V_R=200\text{V}$ , $I_F=2.9\text{A}$ , $di_F/dt=200\text{A}/\mu\text{s}$	-	130	-	ns
	$t_S$		-	12	-	
	$t_F$		-	118	-	
Diode reverse recovery charge	$Q_{rr}$		-	65	-	nC
Diode peak reverse recovery current	$I_{rrm}$		-	1.9	-	A
Diode peak rate of fall of reverse recovery current during $t_b$	$di_{rr}/dt$		-	180	-	$\text{A}/\mu\text{s}$

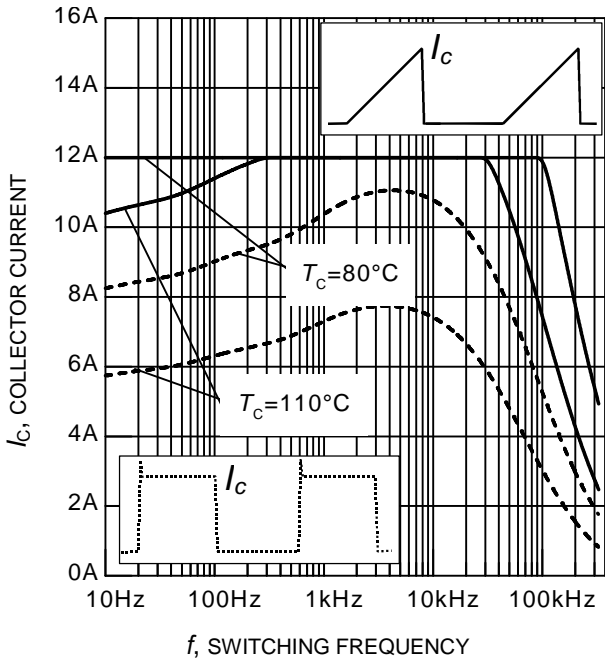
**Switching Characteristic, Inductive Load, at  $T_j=150\text{ }^\circ\text{C}$** 

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>IGBT Characteristic</b>						
Turn-on delay time	$t_{d(on)}$	$T_j=150\text{ }^\circ\text{C}$ $V_{CC}=400\text{V}$ , $I_C=2\text{A}$ , $V_{GE}=0/15\text{V}$ , $R_G=118\Omega$ , $L_{\sigma}^{1)}=180\text{nH}$ , $C_{\sigma}^{1)}=180\text{pF}$ Energy losses include "tail" and diode reverse recovery.	-	20	24	ns
Rise time	$t_r$		-	14	17	
Turn-off delay time	$t_{d(off)}$		-	287	344	
Fall time	$t_f$		-	67	80	
Turn-on energy	$E_{on}$		-	0.054	0.062	mJ
Turn-off energy	$E_{off}$		-	0.043	0.056	
Total switching energy	$E_{ts}$		-	0.097	0.118	

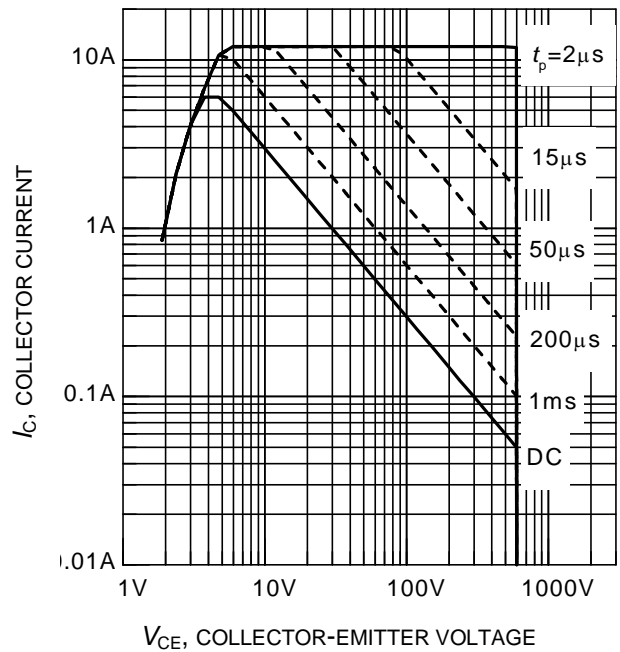
**Anti-Parallel Diode Characteristic**

Diode reverse recovery time	$t_{rr}$	$T_j=150\text{ }^\circ\text{C}$ $V_R=200\text{V}$ , $I_F=2.9\text{A}$ , $di_F/dt=200\text{A}/\mu\text{s}$	-	150	-	ns
	$t_S$		-	19	-	
	$t_F$		-	131	-	
Diode reverse recovery charge	$Q_{rr}$		-	150	-	nC
Diode peak reverse recovery current	$I_{rrm}$		-	3.8	-	A
Diode peak rate of fall of reverse recovery current during $t_b$	$di_{rr}/dt$		-	200	-	$\text{A}/\mu\text{s}$

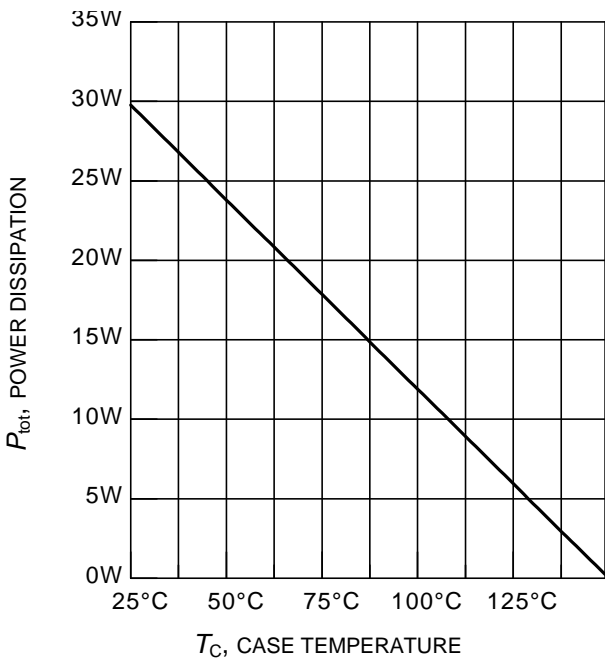
<sup>1)</sup> Leakage inductance  $L_{\sigma}$  and Stray capacity  $C_{\sigma}$  due to dynamic test circuit in Figure E.



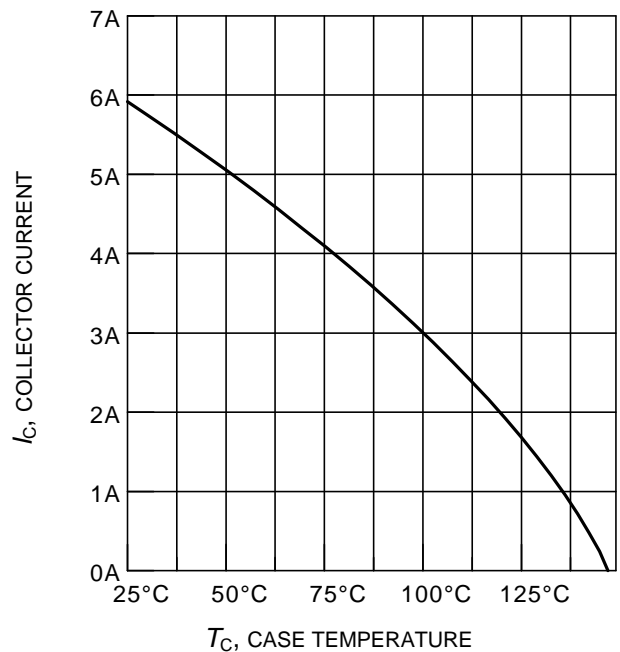
**Figure 1. Collector current as a function of switching frequency**  
 ( $T_j \leq 150^\circ\text{C}$ ,  $D = 0.5$ ,  $V_{CE} = 400\text{V}$ ,  
 $V_{GE} = 0/+15\text{V}$ ,  $R_G = 118\Omega$ )



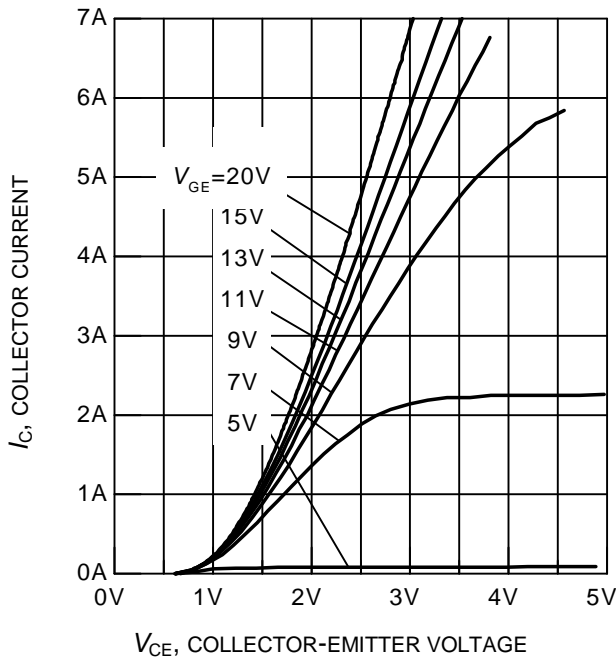
**Figure 2. Safe operating area**  
 ( $D = 0$ ,  $T_C = 25^\circ\text{C}$ ,  $T_j \leq 150^\circ\text{C}$ )



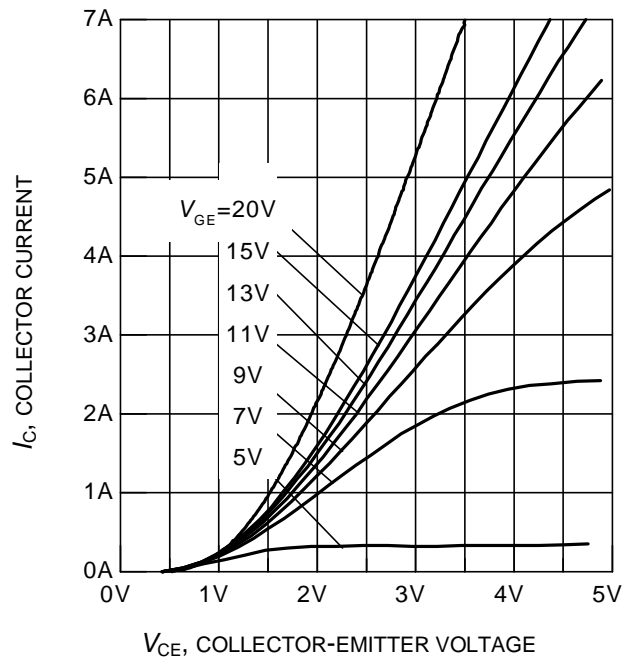
**Figure 3. Power dissipation (IGBT) as a function of case temperature**  
 ( $T_j \leq 150^\circ\text{C}$ )



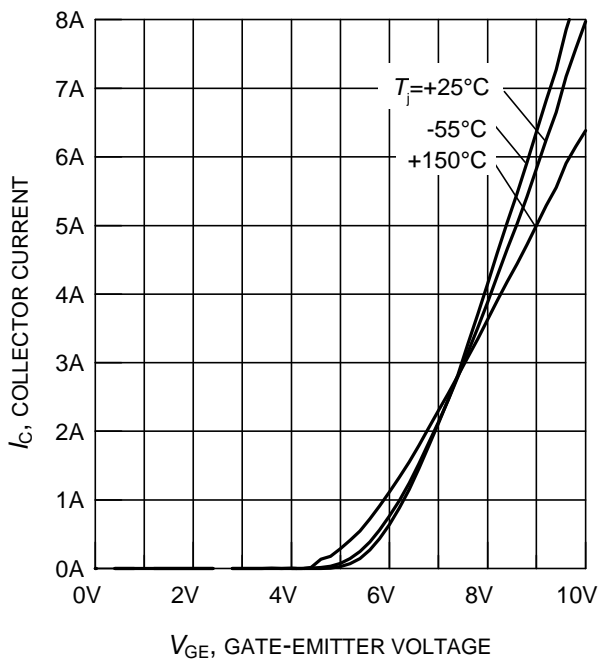
**Figure 4. Collector current as a function of case temperature**  
 ( $V_{GE} \leq 15\text{V}$ ,  $T_j \leq 150^\circ\text{C}$ )



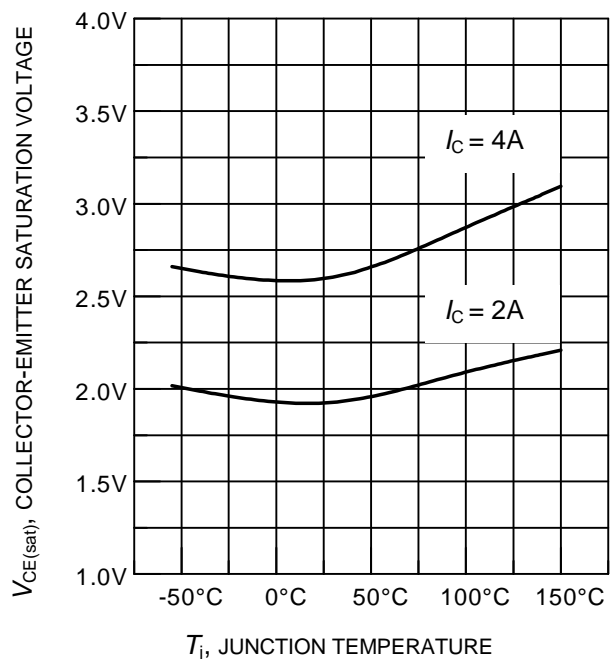
**Figure 5. Typical output characteristics**  
( $T_j = 25^\circ\text{C}$ )



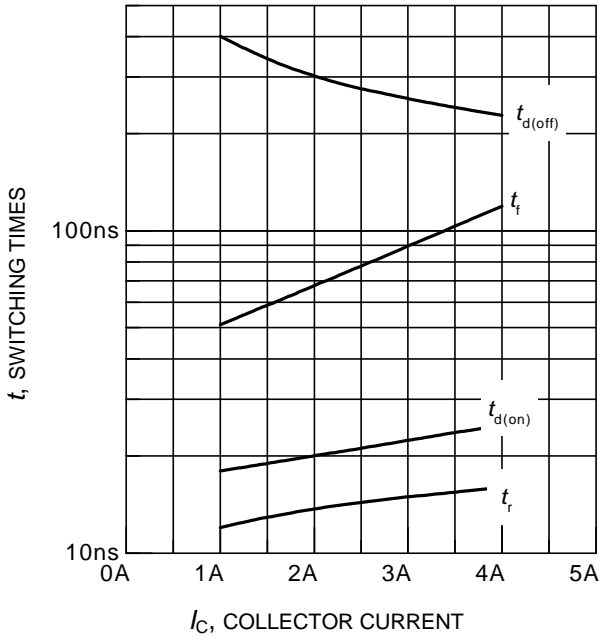
**Figure 6. Typical output characteristics**  
( $T_j = 150^\circ\text{C}$ )



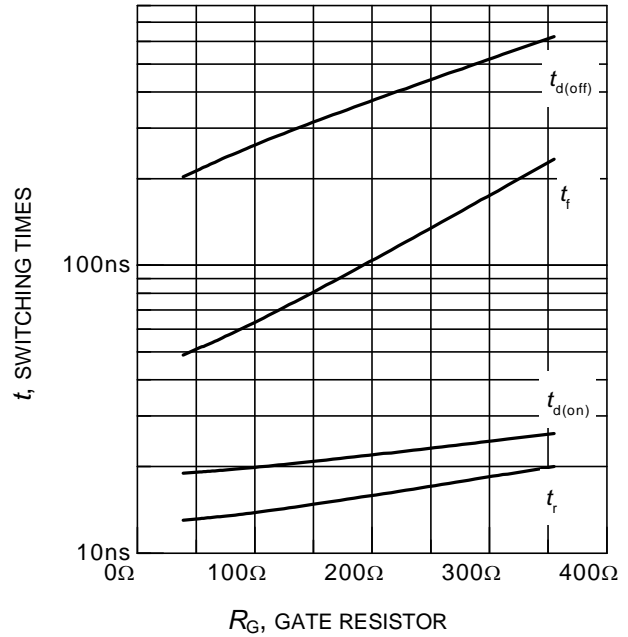
**Figure 7. Typical transfer characteristics**  
( $V_{CE} = 10\text{V}$ )



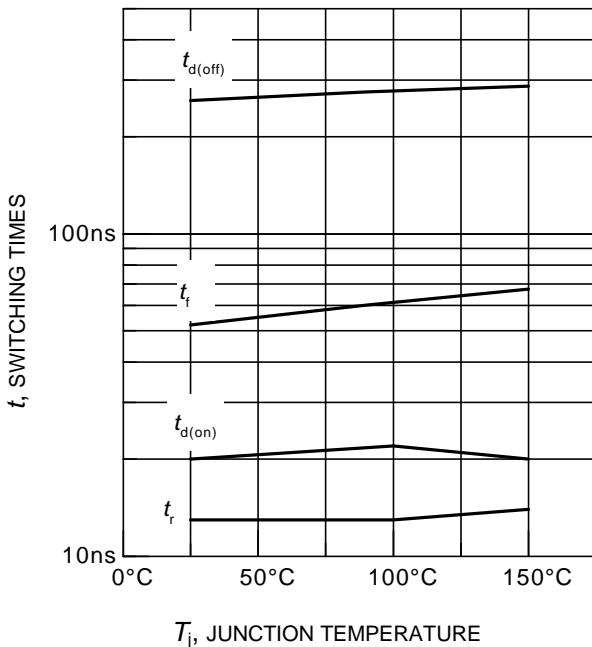
**Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature**  
( $V_{GE} = 15\text{V}$ )



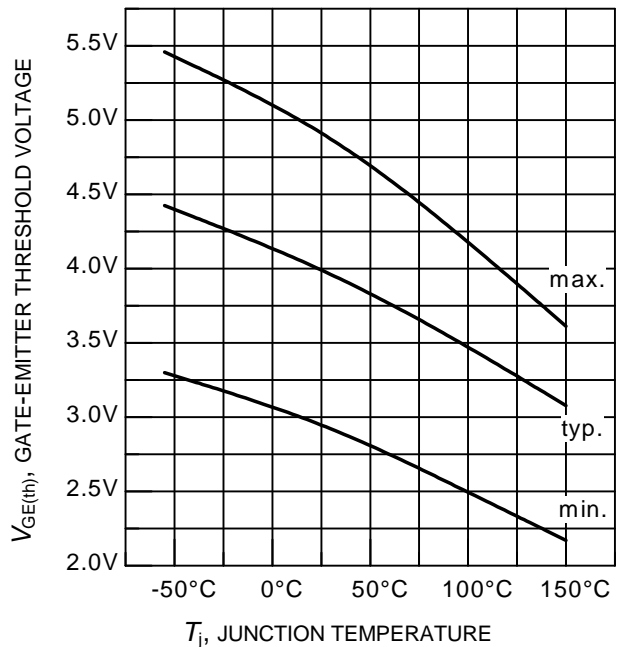
**Figure 9. Typical switching times as a function of collector current**  
 (inductive load,  $T_j = 150^\circ\text{C}$ ,  $V_{CE} = 400\text{V}$ ,  $V_{GE} = 0/+15\text{V}$ ,  $R_G = 118\Omega$ ,  
 Dynamic test circuit in Figure E)



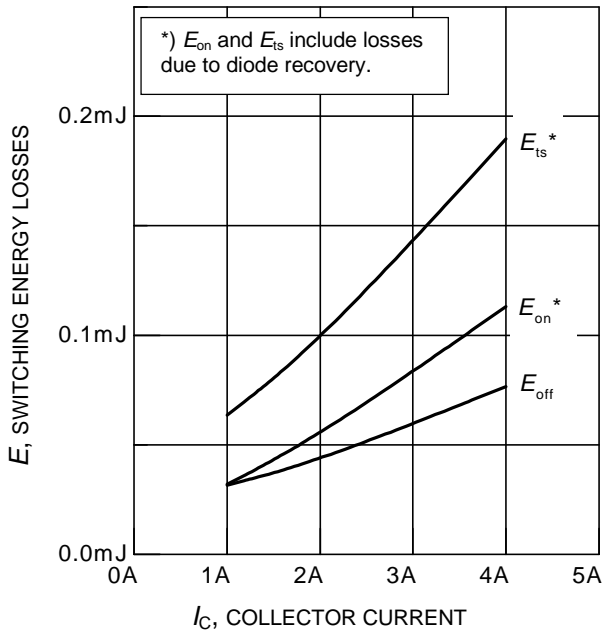
**Figure 10. Typical switching times as a function of gate resistor**  
 (inductive load,  $T_j = 150^\circ\text{C}$ ,  $V_{CE} = 400\text{V}$ ,  $V_{GE} = 0/+15\text{V}$ ,  $I_C = 2\text{A}$ ,  
 Dynamic test circuit in Figure E)



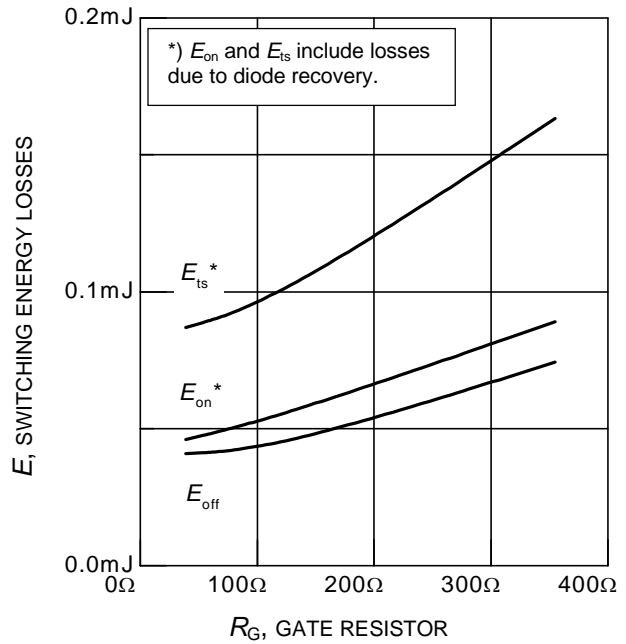
**Figure 11. Typical switching times as a function of junction temperature**  
 (inductive load,  $V_{CE} = 400\text{V}$ ,  $V_{GE} = 0/+15\text{V}$ ,  
 $I_C = 2\text{A}$ ,  $R_G = 118\Omega$ ,  
 Dynamic test circuit in Figure E)



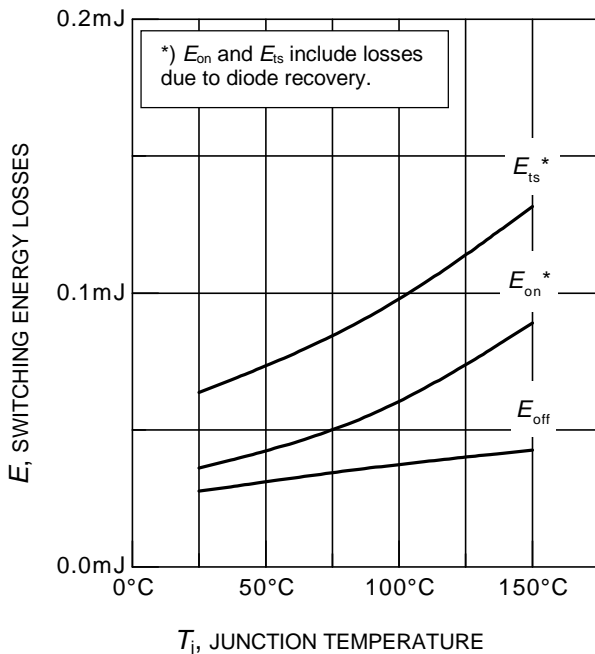
**Figure 12. Gate-emitter threshold voltage as a function of junction temperature**  
 ( $I_C = 0.15\text{mA}$ )



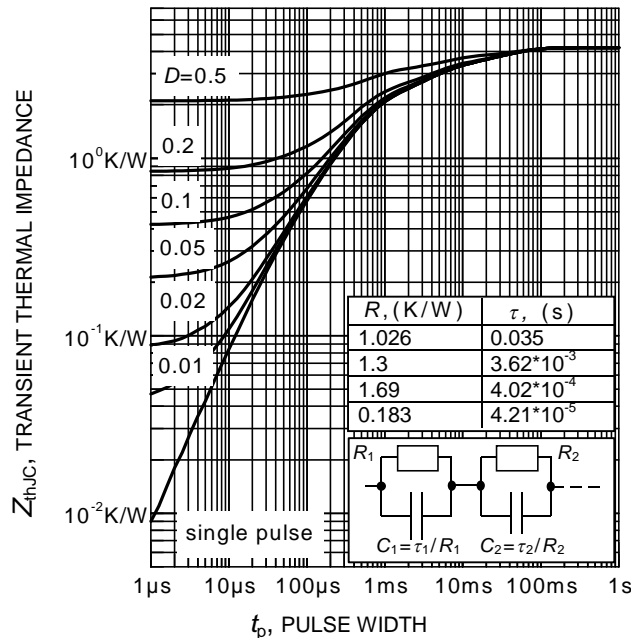
**Figure 13. Typical switching energy losses as a function of collector current**  
 (inductive load,  $T_j = 150^\circ\text{C}$ ,  $V_{CE} = 400\text{V}$ ,  $V_{GE} = 0/+15\text{V}$ ,  $R_G = 118\Omega$ , Dynamic test circuit in Figure E)



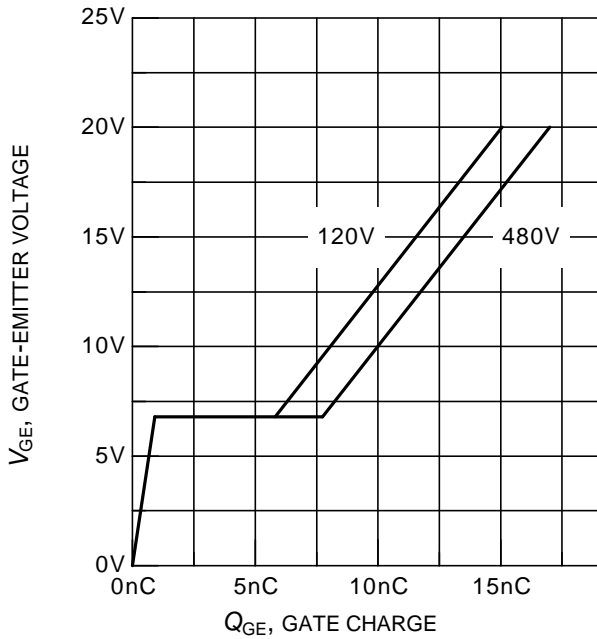
**Figure 14. Typical switching energy losses as a function of gate resistor**  
 (inductive load,  $T_j = 150^\circ\text{C}$ ,  $V_{CE} = 400\text{V}$ ,  $V_{GE} = 0/+15\text{V}$ ,  $I_C = 2\text{A}$ , Dynamic test circuit in Figure E)



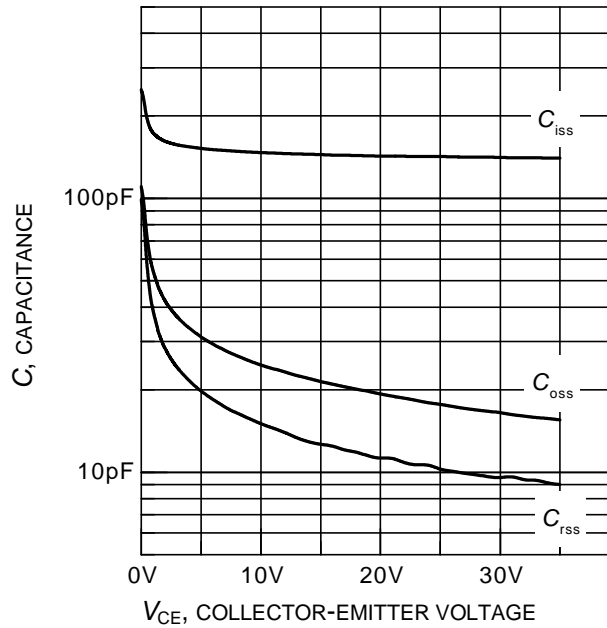
**Figure 15. Typical switching energy losses as a function of junction temperature**  
 (inductive load,  $V_{CE} = 400\text{V}$ ,  $V_{GE} = 0/+15\text{V}$ ,  $I_C = 2\text{A}$ ,  $R_G = 118\Omega$ , Dynamic test circuit in Figure E)



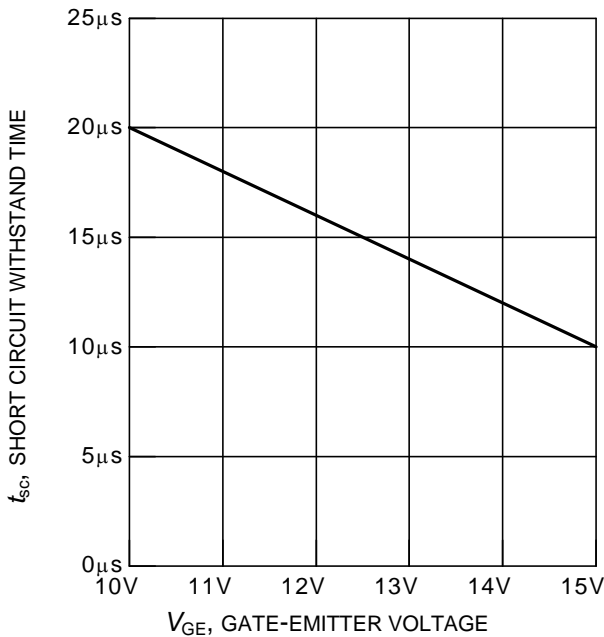
**Figure 16. IGBT transient thermal impedance as a function of pulse width**  
 ( $D = t_p / T$ )



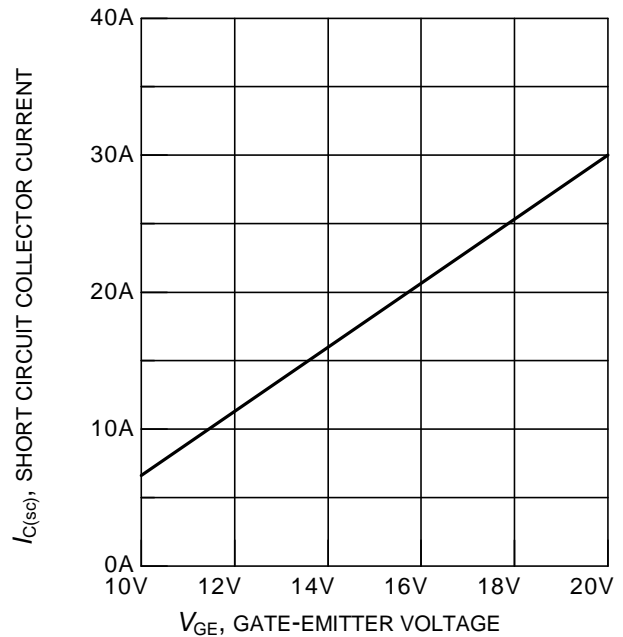
**Figure 17. Typical gate charge**  
( $I_C = 2A$ )



**Figure 18. Typical capacitance as a function of collector-emitter voltage**  
( $V_{GE} = 0V, f = 1MHz$ )

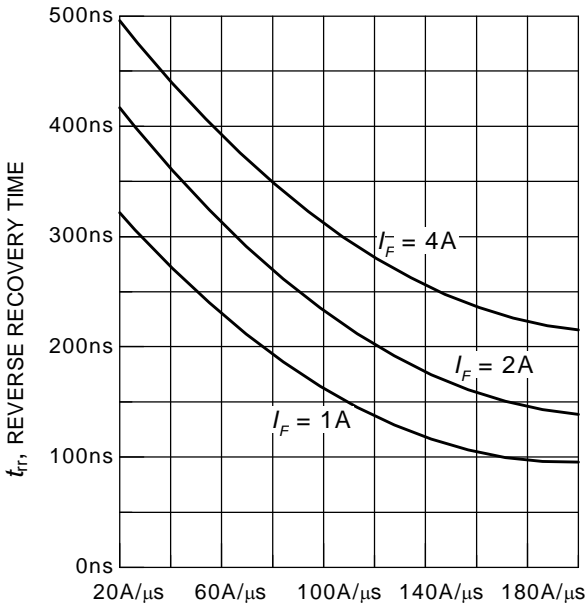


**Figure 19. Short circuit withstand time as a function of gate-emitter voltage**  
( $V_{CE} = 600V, \text{start at } T_j = 25^\circ C$ )

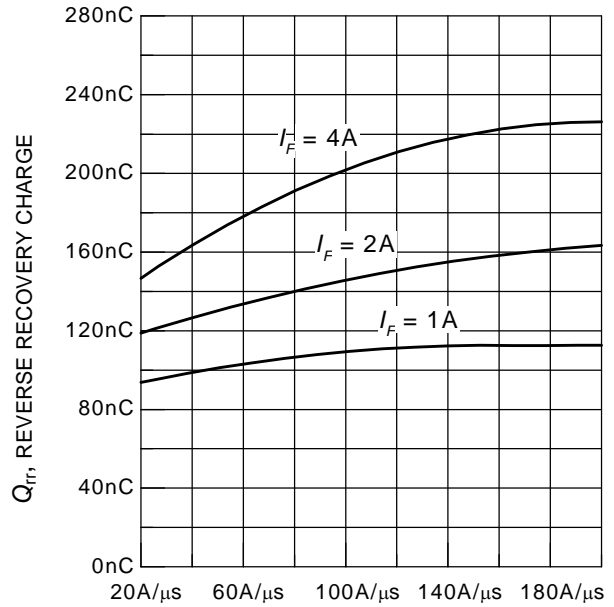


**Figure 20. Typical short circuit collector current as a function of gate-emitter voltage**  
( $V_{CE} \leq 600V, T_j = 150^\circ C$ )

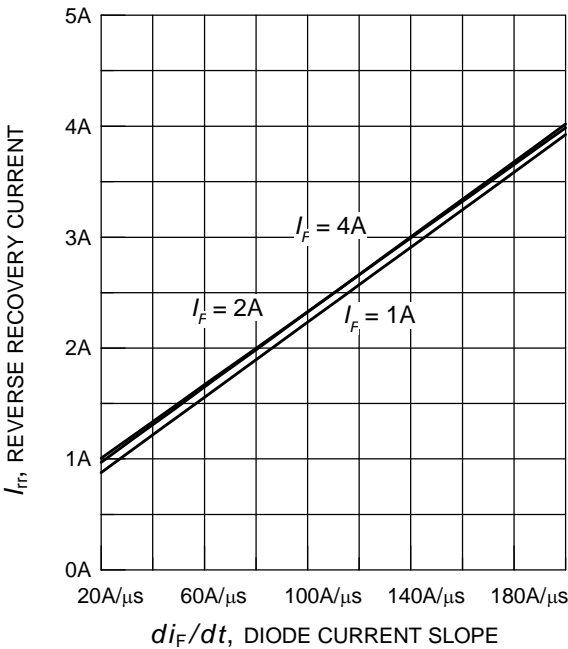




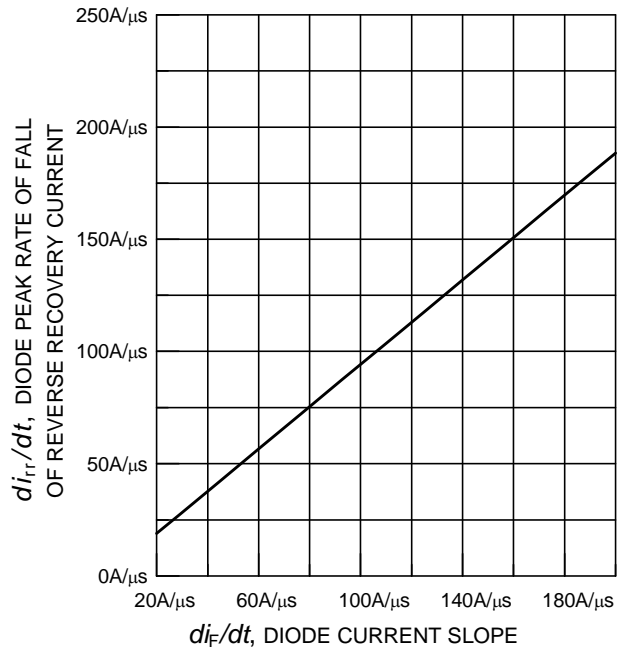
$di_F/dt$ , DIODE CURRENT SLOPE  
**Figure 21. Typical reverse recovery time as a function of diode current slope**  
 ( $V_R = 200V$ ,  $T_j = 125^\circ C$ ,  
 Dynamic test circuit in Figure E)



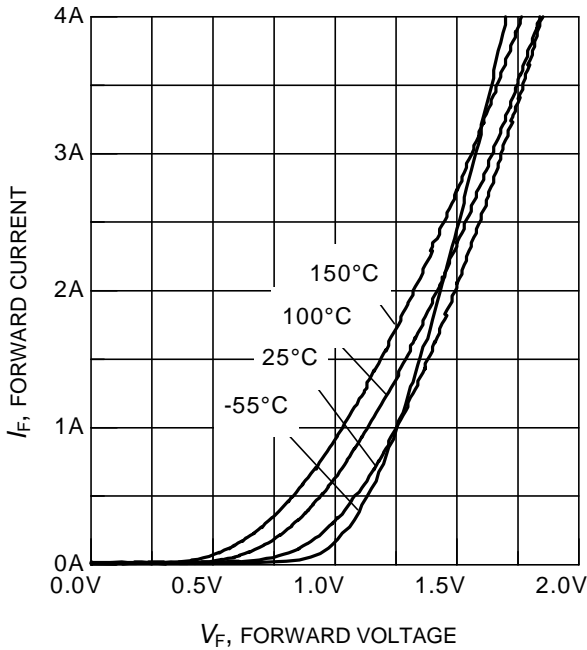
$di_F/dt$ , DIODE CURRENT SLOPE  
**Figure 22. Typical reverse recovery charge as a function of diode current slope**  
 ( $V_R = 200V$ ,  $T_j = 125^\circ C$ ,  
 Dynamic test circuit in Figure E)



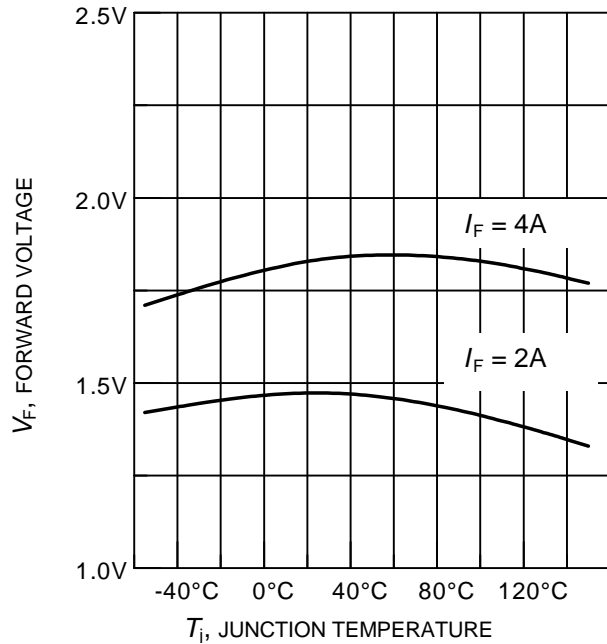
$di_F/dt$ , DIODE CURRENT SLOPE  
**Figure 23. Typical reverse recovery current as a function of diode current slope**  
 ( $V_R = 200V$ ,  $T_j = 125^\circ C$ ,  
 Dynamic test circuit in Figure E)



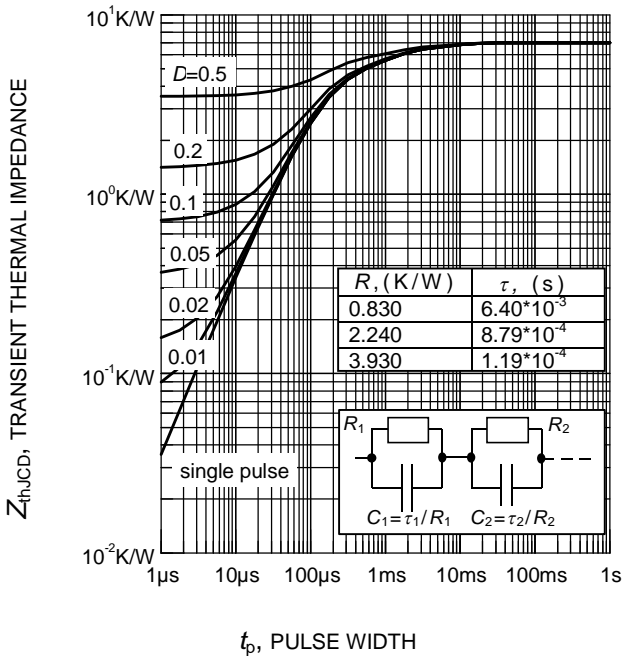
$di_F/dt$ , DIODE CURRENT SLOPE  
**Figure 24. Typical diode peak rate of fall of reverse recovery current as a function of diode current slope**  
 ( $V_R = 200V$ ,  $T_j = 125^\circ C$ ,  
 Dynamic test circuit in Figure E)



**Figure 25. Typical diode forward current as a function of forward voltage**

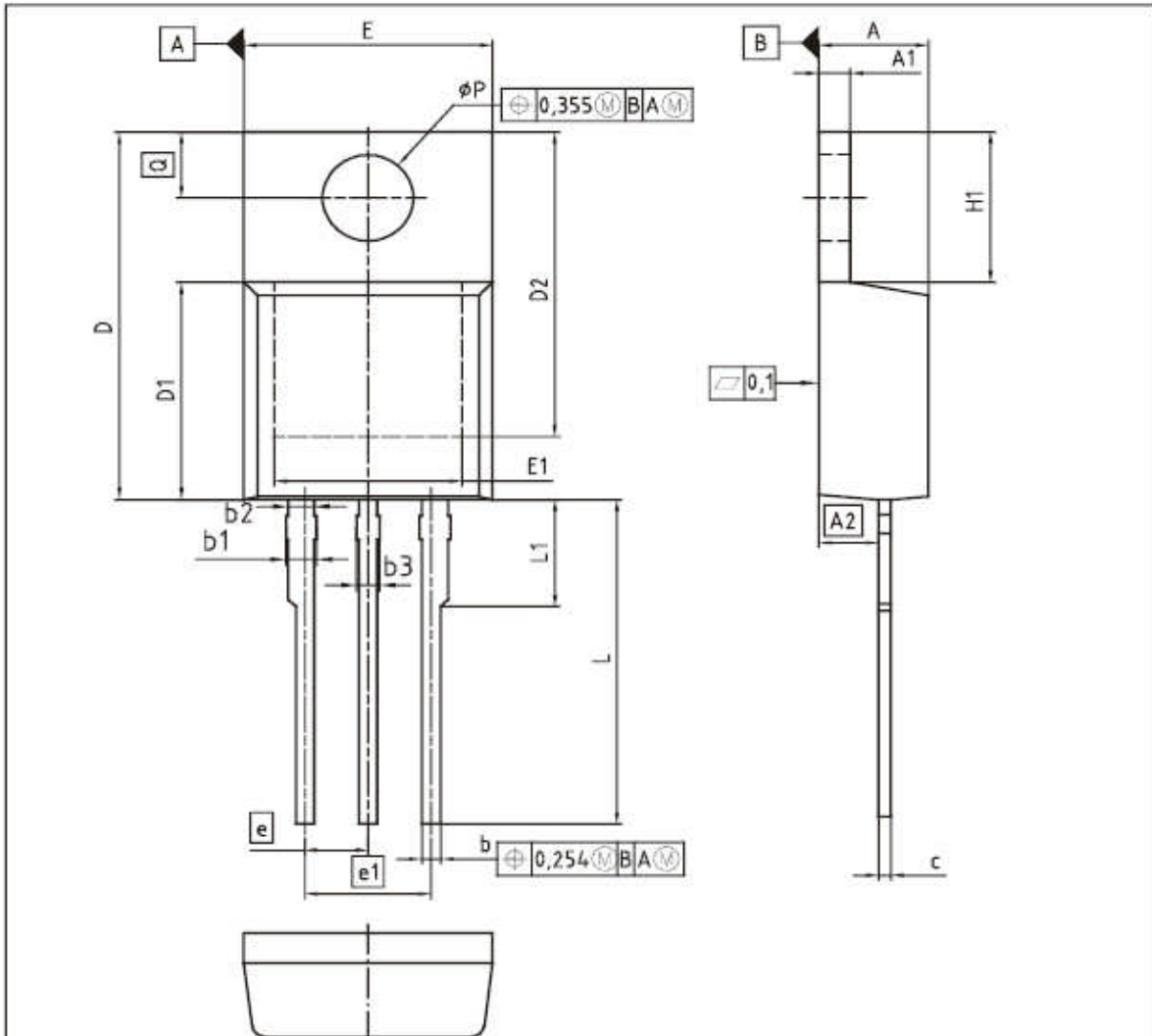


**Figure 26. Typical diode forward voltage as a function of junction temperature**



**Figure 27. Diode transient thermal impedance as a function of pulse width ( $D = t_p / T$ )**

PG-TO220-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4,30	4,57	0,169	0,180
A1	1,17	1,40	0,046	0,055
A2	2,15	2,72	0,085	0,107
b	0,65	0,86	0,026	0,034
b1	0,95	1,40	0,037	0,055
b2	0,95	1,15	0,037	0,045
b3	0,65	1,15	0,026	0,045
c	0,33	0,60	0,013	0,024
D	14,81	15,95	0,583	0,628
D1	8,51	9,45	0,335	0,372
D2	12,19	13,10	0,480	0,516
E	9,70	10,36	0,382	0,408
E1	6,50	8,60	0,256	0,339
e	2,54		0,100	
e1	5,08		0,200	
N	3		3	
H1	5,90	6,90	0,232	0,272
L	13,00	14,00	0,512	0,551
L1	-	4,80	-	0,189
$\phi P$	3,60	3,89	0,142	0,153
Q	2,60	3,00	0,102	0,118

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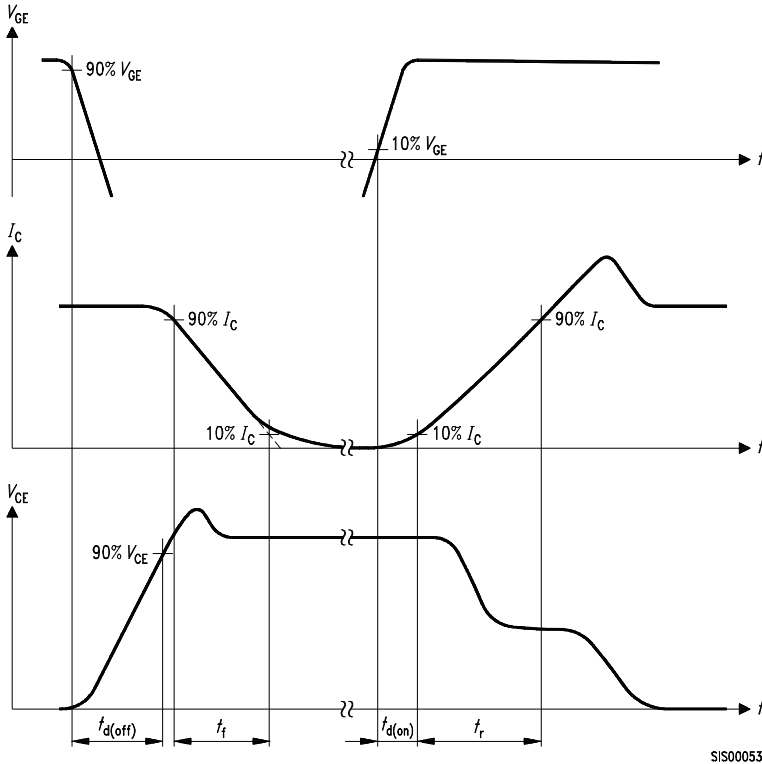


Figure A. Definition of switching times

SIS00053

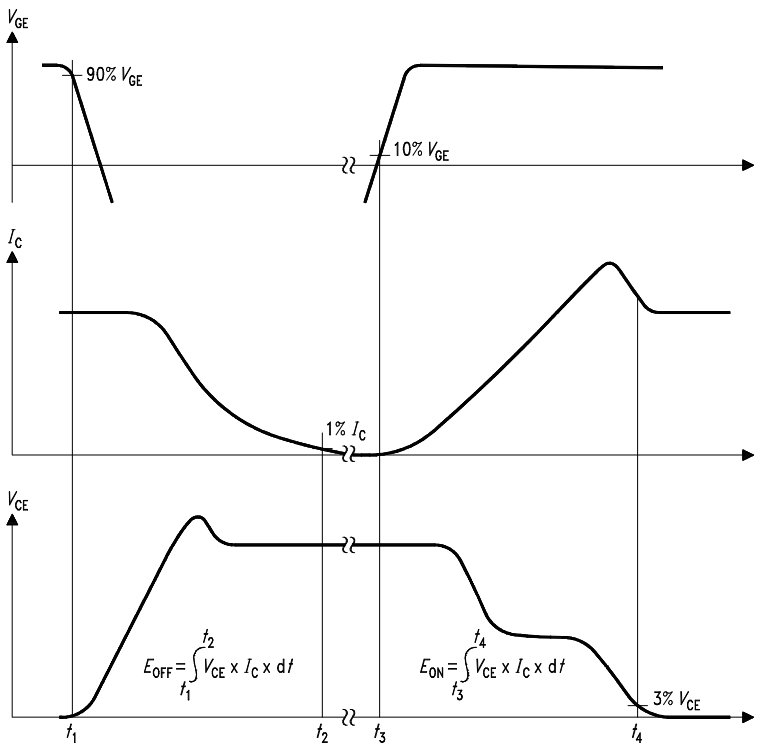


Figure B. Definition of switching losses

SIS00050

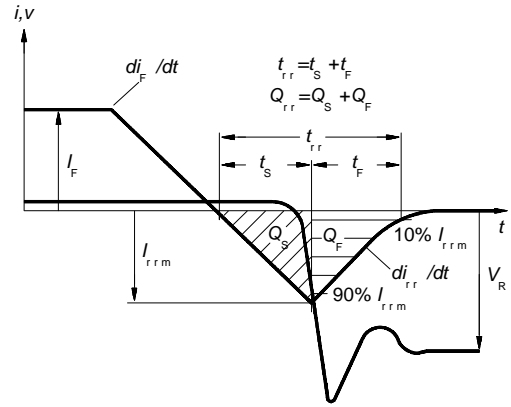


Figure C. Definition of diodes switching characteristics

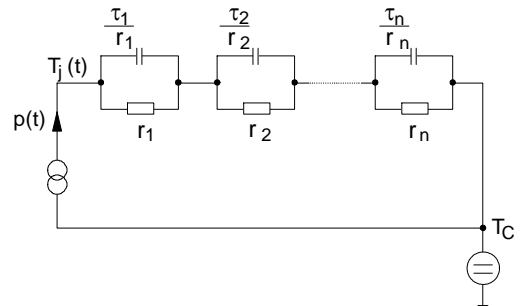


Figure D. Thermal equivalent circuit

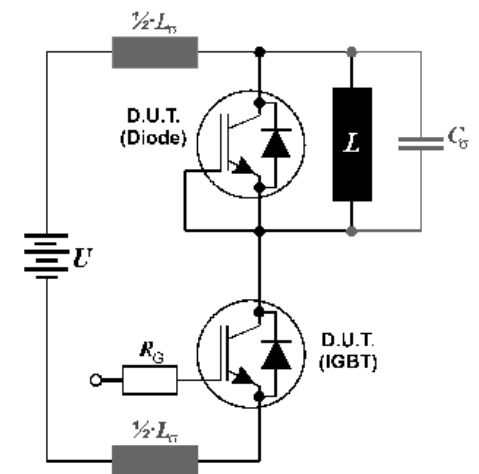


Figure E. Dynamic test circuit  
Leakage inductance  $L_{\sigma} = 180\text{nH}$   
and Stray capacity  $C_{\sigma} = 180\text{pF}$ .

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